

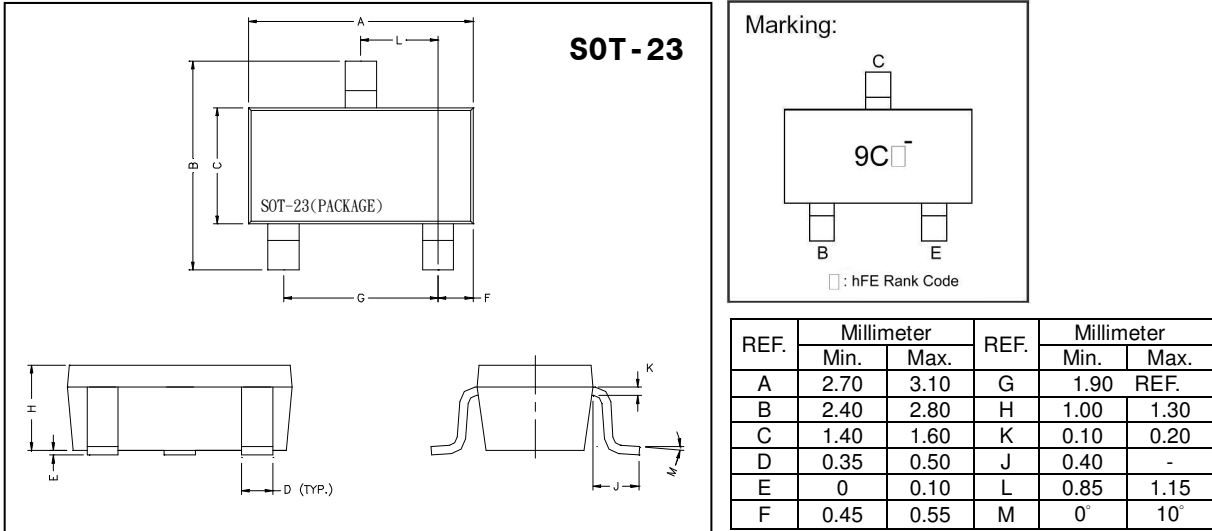
GBC858

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The GBC858 is designed for switching and AF amplifier application, suitable for automatic insertion in thick and thin-film circuits.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	-30	V
Collector to Emitter Voltage	VCEO	-30	V
Emitter to Base Voltage	VEBO	-5	V
Collector Current	IC	-100	mA
Total Power Dissipation	PD	225	mW

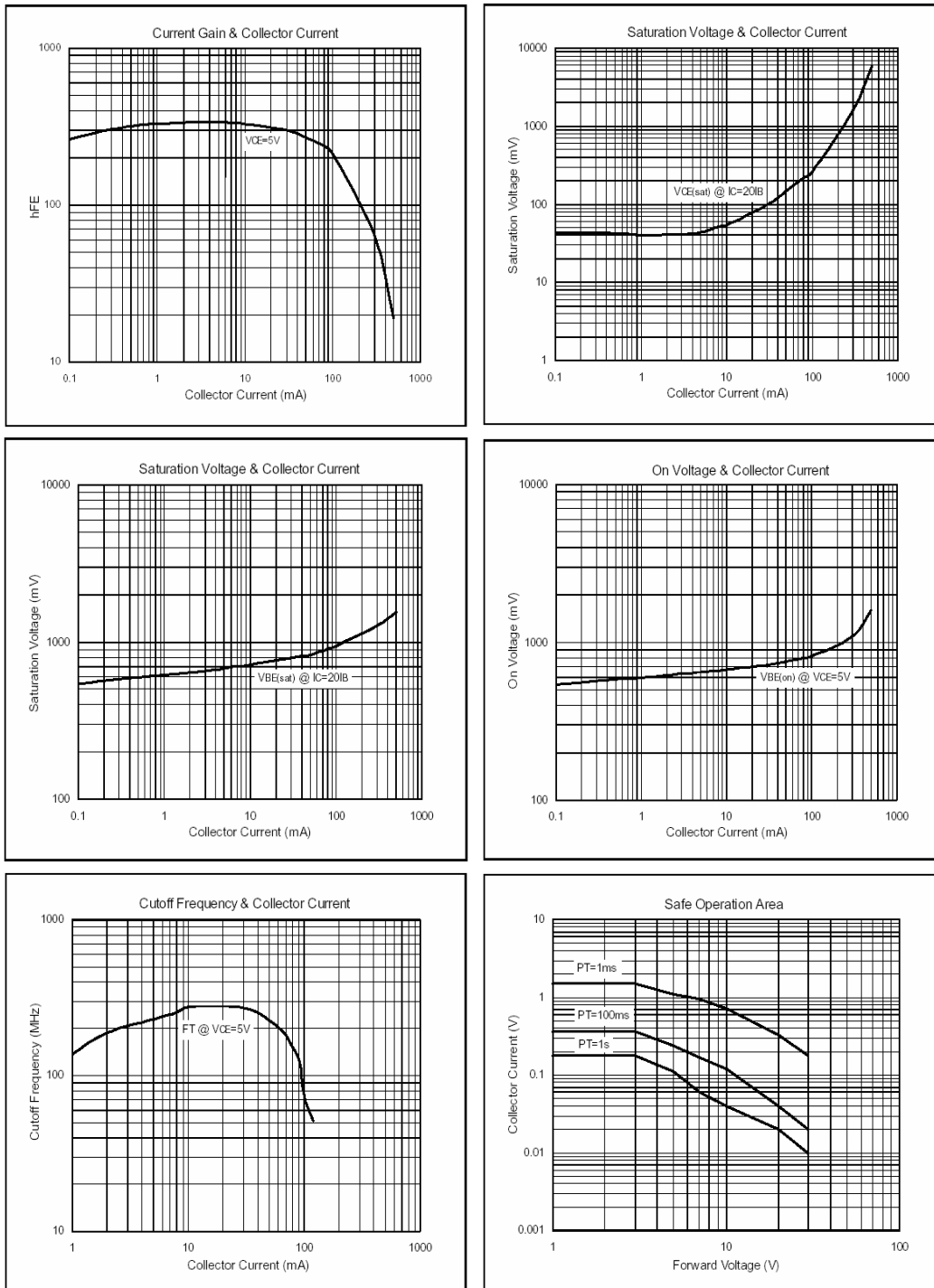
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-30	-	-	V	IC=-100uA
BVCEO	-30	-	-	V	IC=-1mA
BVEBO	-5	-	-	V	IE=-10uA
ICBO	-	-	-15	nA	VCB=-30V
VCE(sat)1	-	-90	-300	mV	IC=-10mA, IB=-0.5mA
VCE(sat)2	-	-250	-650	mV	IC=-100mA, IB=-5mA
VBE(sat)1	-	-700	-	mV	IC=-10mA, IB=-0.5mA
VBE(sat)2	-	-900	-	mV	IC=-100mA, IB=-5mA
VBE(on)1	-600	-	-750	mV	VCE=-5V, IC=-2mA
VBE(on)2	-	-	-800	mV	VCE=-5V, IC=-10mA
hFE	110	-	800		VCE=-5V, IC=-2mA
fT	-	150	-	MHz	VCE=-5V, IC=-10mA
Cob	-	-	6	pF	VCB=-10V, f=1MHz, IE=0A

Classification Of hFE

Rank	A	B	C
hFE	110-220	200-450	420-800

Characteristics Curve



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